NSN 5961-00-131-1197

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Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-131-1197 **Inclosure Material:** Metal **Overall Length:** 0.230 inches **Mounting Facility Quantity: Electrode Internally-electrically Connected To Case:** Cathode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 0.424 inches and 0.437 inches **Thread Size:** 0.190 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 100.0 working peak reverse voltage, peak total value and 200.0 nonrepetitive peak reverse voltage, peak total value and 70.0 reverse voltage, total rms **Current Rating Per Characteristic:** 75.00 amperes forward current, repetitive, peak total value and 200.00 amperes forward current, nonrepetitive, peak total value **Maximum Operating Tempurature Per Measurement Point:** 190.0 degrees celsius junction **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 1 wire hook Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: